

Curriculum vitae: Dr. Vinay Kumar M

Assistant Professor
Department of Physics
K.L.E's R.L.Science Institute (Autonomous),
Belagavi-590001

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Academic Qualifications:

- ➤ **Ph.D** from University of Mysore (2018).
- **KSET** (Karnataka State Eligibility Test for Lecturer/Assistant professorship) qualified (2015).
- ➤ M.Sc Physics (Nuclear Physics Specialization) from University of Mysore (2009).

PhD Thesis Title: "Influence of radiation induced defects on electronic properties of some semiconductor devices"

PhD Supervisor: Dr. S. Krishnaveni Associate Professor, DOS in Physics, Manasagangotri, UOM, Mysore.

Current Positions:

- ➤ Deputy Controller of Examinations, K.L.E's R.L.Science Institute (Autonomous), Belagavi-590001.
- Chairman, Physical Society, K.L.E's R.L.Science Institute (Autonomous), Belagavi-590001.
- Nodal Officer AISHE, K.L.E's R.L.Science Institute (Autonomous), Belagavi-590001.

Teaching Experience:

- ➤ Feb. 2010 to May 2011: Assistant Professor, Department of Physics, PES College of Science Arts and Commerce, Mandya-571401.
- ➤ Oct. 2014 to May 2019 : Assistant Professor, Department of Physics, Post graduate and Research Center, Bharathi College, Bharathinagara, Mandya Dist-571422.
- ➤ June 2019 to till date: Assistant Professor, Department of Physics, K.L.E's R.L.Science Institute (Autonomous), Belagavi-590001.

Awards:

- ➤ Dec 2011- Nov 2012: J. R.F IUAC Research Project, New Delhi.
- ➤ Dec 2012- Sep 2014: S. R.F IUAC Research Project, New Delhi.

- ➢ Best Poster Award for the paper "30 and 60 MeV Boron Ion Irradiation Effects on Electrical Characteristics of Bipolar Transistor", K. S. Krishna Kumar, C.M. Dinesh, Ramani, S.A. Khan, M.Vinay Kumar, S. Krishnaveni, B. Jayashree, Ist International conference on Physics of Materials and Material Based Device Fabrication, 17th -19th January 2012, Shivaji University, Kolhapur, India
- ➤ Secured Best Oral Presentation (III Place) Award for the paper "Modification In Electrical Properties Of Silicon Photo-Detector Due To 100MeV Si ⁷⁺ Ion Irradiation" at National conference on Solar Energy and its Application (NCSEA2013) on 9th April 2013 at Maharani's science college for women, Bangalore-560001

Research Interests:

Reliability Studies in Semiconductors, Ion beam induced modifications, Defects in semiconductors, Fabrication of Semiconductor devices and simulation studies.

Papers Presented in National/International symposia/conferences:

- 60 and 100 MeV Oxygen Ion Irradiation Effects on Electrical Characteristics of Bipolar Transistor, K. S. Krishakumar, C.M. Dinesh, Ramani, M. Vinay Kumar, S. Krishnaveni, M. C. Radhakrishna, B. Jayashree International Workshop on the Physics of Semiconductor Devices, Dec.19-22,2011. IIT Kanpur, Kanpur India.
- Effect of 100MeV oxygen ion irradiation on silicon NPN power transistor, M. Vinay Kumar, K. S.Krishnakumar, C.M.Dinesh, S.Krishnaveni Ramani,56th DAE SSPS, 19–23 December 2011, SRM University, Kattankulathur, Tamilnadu, India.
- 3. Best Poster Award for the paper "30 and 60 MeV Boron Ion Irradiation Effects on Electrical Characteristics of Bipolar Transistor", K. S. Krishna Kumar, C.M. Dinesh, Ramani, S.A. Khan, M.Vinay Kumar, S. Krishnaveni, B. Jayashree, Ist International conference on Physics of Materials and Material Based Device Fabrication, 17th -19th January 2012, Shivaji University, Kolhapur, India.
- 4. "Effect of 60 MeV Boron Ion Irradiation on Silicon NPN Power Transistor", **M. Vinay Kumar**, K. S. Krishnakumar, C.M. Dinesh, B. Jayashree, Ramani, S. Krishnaveni, Ist International

- conference on Physics of Materials and Material Based Device Fabrication, 17th -19th January 2012, Shivaji University, Kolhapur, India.
- 5. Secured Best Oral Presentation (III Place) Award for the paper "MODIFICATION IN ELECTRICAL PROPERTIES OF SILICON PHOTO-DETECTOR DUE TO 100mev Si ⁷⁺ ION IRRADIATION" at National conference on Solar Energy and its Application (NCSEA2013) on 9th April 2013 at Maharani's science college for women, Bangalore-560001
- "A Comparative study of 30MeV Boron4+ and 60MeV Oxygen8+ ion irradiated Si NPN BJTs",
 M. Vinay Kumar, T. Yashoda, C. M. Dinesh, B. Jayashree, Ramani, S. Krishnaveni, DAE-SSPS 2014, VIT Vellore, Tamilnadu, India.
- 7. "Insitu Current transport studies on 100MeV Oxygen ion irradiated Si Photodetector", **M. Vinay Kumar**, Shammi Verma, K Asokan, T. Yashoda, B. Jayashree, Ramani, S. Krishnaveni, DAE-SSPS 2014, VIT Vellore, Tamilnadu, India.
- 8. **M.Vinay Kumar**, Santosh Kumar, T.Yashoda and S.Krishnaveni "SHI induced damage in Electrical properties of silicon NPN BJT's" 60th DAE -SSPS 2015.
- 9. Santosh Kumar, **M Vinay Kumar**, Manjunatha Pattabi, Asokan K, B. N. Chandrashekar, Cheng chun & S Krishnaveni "Effect of Gamma irradiation on Electrical Properties of CdTe/CdS Solar Cells", International Conference on Advances in Science and Engineering, January 20-22, 2017, Bangkok, Thailand. (in process of publication Elsevier Materials today Proceedings)
- 10. Santosh Kumar, M Vinay Kumar, Manjunatha Pattabi, Asokan K, Xavier, Nini, Martin and S Krishnaveni "Gamma irradiation effects on Electrical Properties of CdTe/CdS Solar Cells" International Symposium on Advanced Materials for Engineering Applications (ISAMEA-2017), March 24-25, 2017, NIE Mysuru.
- 11. M. Vinay Kumar, Santosh Kumar, S. Madan Kumar, K. Byrappa, S. Krishnaveni, S.P. Karanth, V. Shobha, and k asokan "Electrical characteristics of 100MeV O7+ Ion Beam irradiated Si Photo detectors National Conference on particle accelerators in interdisciplinary research (pair), April 11-13, 2017, Department of Physics, Mangalore University, Mangalagangotri-574199 Mangalore, Karnataka.
- 12. Santosh Kumar, **M Vinay Kumar**, Manjunatha Pattabi, Asokan K, Xavier, Nini, Martin & S Krishnaveni, "Effect of high dose Gamma irradiation on Electrical Properties of CdTe/CdS Solar

- Cells" National Symposium on Nano Science and Technology (NSNST-2017), 02-Jul-2017 to 04-Jul-2017, IISc Banglore, Karnataka.
- 13. Santosh Kumar, **M Vinay Kumar**, Asokan K, & S Krishnaveni "Effect of high dose Gamma irradiation on Electrical Properties of GaAs infrared emitting diode (IRED)" National Conference on Science and Technology-Reaching the Unreached-Recent advances in Physical, Chemical, Mathematical and Biological Sciences for Energy, Health and Environment, 8th–9thSeptember, 2017, Mangalore University, Mangalagangotri-574199 Mangalore, Karnataka.
- 14. Santosh Kumar, M Vinay Kumar, Asokan K, & S Krishnaveni "Effect of High Dose Gamma Irradiation on Electrical Properties of commercial GaN and GaAs based Optoelectronic Devices" National Seminar on "Recent Trends in Physics (NSRTP-2017), 26 September 2017, Bharathi College Mandya, Karnataka.

Research Papers in International Peer reviewed journals:

- Vinay Kumar, M., Verma, S., Shobha, V., Jayashree, B., Kanjilal, D., Ramani, R., & Krishnaveni, S. (2014). 100 MeV Si⁷⁺ Ion Irradiation Induced Modifications in Electrical Characteristics of Si Photo Detector: An In-Situ Reliability Study. *Journal of Materials Science Research*, 3(3), 24.
- 2. **Vinay Kumar, M.**, Verma, S., Asokan, K., Shobha, V., Karanth, S. P., & Krishnaveni, S. (2016). In Situ electrical characteristics of 150 MeV Ag⁹⁺ Ion Beam induced damage in Si photo detector. *ECS Journal of Solid State Science and Technology*, *5*(7), P384-P388.
- 3. **Vinay Kumar**, **M.**, Santosh kumar., Chun Cheng., Asokan, K., Shobha, V., Karanth, S. P., & Krishnaveni, S. (2017). Influence of High Dose Gamma Irradiation on Electrical Characteristics of Si Photo Detectors. *ECS Journal of Solid State Science and Technology*, 6(10), Q132-Q135.
- 4. **Vinay Kumar, M.**, Krishnakumar, K. S., Dinesh, C. M., Krishnaveni, S., & Ramani. (2012, June). Effect of 100 MeV oxygen ion irradiation on silicon NPN power transistor. In *AIP Conference Proceedings* (Vol. 1447, No. 1, pp. 1085-1086). AIP Publishing.
- Vinay Kumar, M., Yashoda, T., Dinesh, C. M., Krishnakumar, K. S., Jayashree, B., Ramani, & Krishnaveni, S. (2015, June). A comparative study of 30MeV boron4+ and 60 MeV oxygen 8+ ion irradiated Si NPN BJTs. In *AIP Conference Proceedings* (Vol. 1665, No. 1, p. 120039). AIP Publishing.

- 6. **Vinay Kumar, M.**, Kumar, S., Yashoda, T., & Krishnaveni, S. (2016, May). SHI induced damage in electrical properties of silicon NPN BJTs. In *AIP Conference Proceedings* (Vol. 1731, No. 1, p. 120031). AIP Publishing.
- 7. Santosh Kumar, **Vinay Kumar M.**, ManjunathaPattabi, Asokan K., Xavier, Nini, Martin, ChandrashekarB. N., Cheng Chun, Krishnaveni S. Effect of Gamma Irradiation on Eelectrical properties of CdTe/Cds Solar cells. Proceedings of Materials Today, 5, P22570-75, 2018.
- 8. Santosh Kumar, **Vinay Kumar M**, Srinivas R. N., Krishnaveni S. Electrical characterization of Ni/nGaN Schottky diodes, IEEE Digital Library, P356-358, ISBN 978-93-5291- 953-6, 2018.
- Krishnaveni Sannathammegowda Santosh Kumar, Xiang Zhang , Vinay Kumar Mariswamy , Varra Rajagopal Reddy , Asokan Kandasami , Arun Nimmala , S V S Nageswara Rao , Jue Tang, Seeram Ramakrishnna. Medium Energy Carbon and Nitrogen Ion Beam Induced Modifications in Charge Transport, Structural and Optical Properties of Ni/Pd/n-GaN Schottky Barrier Diodes. MDPI, Materials, 13(6), 1299, 2020.
- 10. Santosh Kumar, **Vinay Kumar M**, and Krishnaveni S. Fabrication and analysis of the current transport mechanism of Ni/n-GaN Schottky barrier diodes through different models *Semiconductors*, *Springer*,169–175, 54 (2020).

Technical Skills:

Operating Systems	⇧	Dos, Linux, Windows 9x/2000/Xp/7
Languages	₽	С
Packages	₽	MS-office, Latex, Beamer

Membership in Professional bodies:

➤ Life Member - Indian Association of Physics Teachers.

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